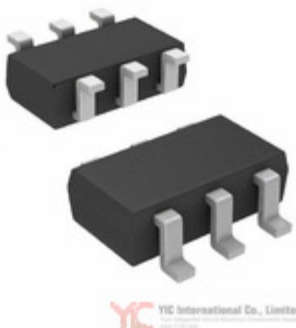

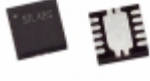
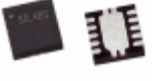
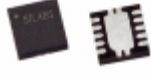



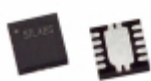

	<h2 style="color: #E67E22;">SI3460BDV-T1-E3</h2>
 <p>Image may be representation. See specs for product details.</p>	Hersteller-Teilenummer: SI3460BDV-T1-E3
	Hersteller / Marke: Electro-Films (EFI) / Vishay
	Teil der Beschreibung: MOSFET N-CH 20V 8A 6-TSOP
	Datenblätter:  SI3460BDV-T1-E3.pdf
	RoHs Status: Bleifrei / RoHS-konform
	Lagerzustand: New original, 58074 pcs Stock Available.
Liefern von: Hong Kong	
Versandweg: DHL/Fedex/TNT/UPS/EMS	

Spezifikationen

Teilenummer	SI3460BDV-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 20V 8A 6-TSOP
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	58074 pcs Stock
Hersteller Standard Vorlaufzeit	33 Weeks
detaillierte Beschreibung	N-Channel 20V 8A (Tc) 2W (Ta), 3.5W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SOT-23-6 Thin, TSOT-23-6
Supplier Device-Gehäuse	6-TSOP
Verlustleistung (max)	2W (Ta), 3.5W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	8A (Tc)
Rds On (Max) @ Id, Vgs	27 mOhm @ 5.1A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	24nC @ 8V
Eingabekapazität (Ciss) (Max) @ Vds	860pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Original-Reel®
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI3460BDV-T1-E3DKR













SI3460BDV-T1-E3 ist neu im Original. Suche SI3460BDV-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI3460BDV-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI3460BDV-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI3460-E03-GM Energy Micro (Silicon Labs) IC POWER MANAGEMENT CTLR 11VQFN</p>	 <p>SI3460-E02-GM Energy Micro (Silicon Labs) IC POWER MANAGEMENT CTLR 11VQFN</p>	 <p>SI3460-E02-GMR Energy Micro (Silicon Labs) IC POWER MANAGEMENT CTLR 11VQFN</p>	 <p>SI3460BDV-T1-E3 Vishay / Siliconix MOSFET N-CH 20V 8A 6-TSOP</p>
 <p>SI3460BDV-T1-GE3 Vishay / Siliconix MOSFET N-CH 20V 8A 6-TSOP</p>	 <p>Si3460DDV Vishay Si3460DDV Vishay</p>	 <p>SI3460-E03-GMR Energy Micro (Silicon Labs) IC POWER MANAGEMENT CTLR 11VQFN</p>	 <p>Si3460DDV-T1-E3 Son Son TSOP-6</p>

heiße Teile

Mehr

 SI3457CDV-T1-GE3	 SI3457DV	 SI3457DV	 SI3457DV-T1	 SI3457DV-T1-E3
 SI3457DV-T1-GE3	 SI3457DV-T1-E3	 SI3458BDV-T1-E3	 SI3458BDV-T1-E3	 SI3458BDV-T1-GE3
 SI3458BDV-T1-GE3	 SI3458DV-T1-E3	 SI3458DV-T1-E3	 SI3458DV-T1-GE3	 SI3459BDV-T1-E
 SI3459BDV-T1-E3	 SI3459BDV-T1-E3	 SI3459BDV-T1-GE3	 SI3459BDV-T1-GE3	 SI3459DV-T1-E3
 SI3459DV-T1-E3	 SI3459DV-T1-GE3	 SI3460-E02-GMR	 SI3460-E03-GMR	 SI3460BDV-T1-E3
 SI3460BDV-T1-GE3	 SI3460BDV-T1-GE3	 SI3460DDV	 SI3460DDV-T1-GE3	 SI3460DDV-T1-GE3
 SI3460DV	 SI3460DV-T1	 SI3460DV-T1-E3	 SI3460DV-T1-E3	 SI3460DV-T1-GE3
 SI3460DV-T1-GE3	 SI3461DV-T1-E3	 SI3461DVT1-GE3	 SI3464DV	 SI3464DV-T1-GE3
 SI3464DV-T1-GE3	 SI3465DV-T1-E3	 SI3465DV-T1-E3	 SI3465DV-T1-GE3	 SI3465DV-T1-GE3
 SI3467DV	 SI3467DV-T1-E3	 SI3467DV-T1-E3	 SI3467DV-T1-GE3	 SI3467DV-T1-GE3

Contact us: Info@Y-IC.com

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